

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

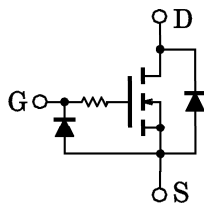
2SK1827

HIGH SPEED SWITCHING APPLICATIONS

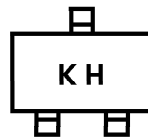
ANALOG SWITCH APPLICATIONS

- 4V Gate Drive
- Low Threshold Voltage : $V_{th} = 0.8 \sim 2.5V$
- High Speed
- Enhancement-Mode
- Small Package

EQUIVALENT CIRCUIT

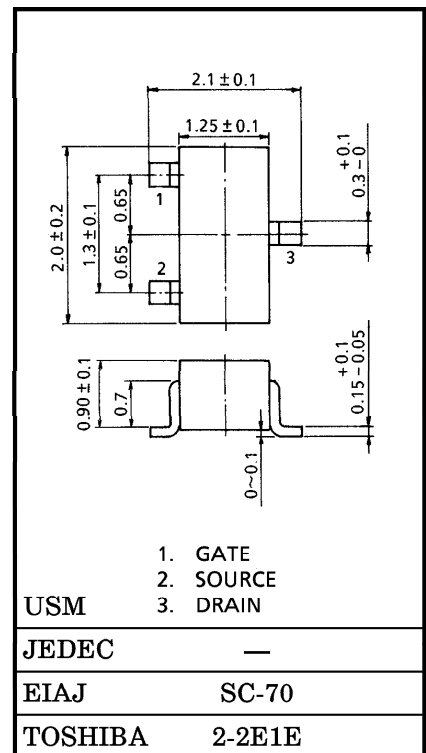


MARKING



This transistor is electrostatic sensitive device.
Please handle with caution.

Unit in mm



Weight : 0.006g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GSS}	10	V
DC Drain Current	I_D	50	mA
Drain Power Dissipation	P_D	100	mW
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

000707EAA1

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	IGSS	VGS=10V, VDS=0	—	—	1	μA	
Drain-Source Breakdown Voltage	V(BR)DSS	ID=100μA, VGS=0	50	—	—	V	
Drain Cut-off Current	IDSS	VDS=50V, VGS=0	—	—	1	μA	
Gate Threshold Voltage	Vth	VDS=5V, ID=0.1mA	0.8	—	2.5	V	
Forward Transfer Admittance	Yfs	VDS=5V, ID=10mA	20	—	—	mS	
Drain-Source ON Resistance	RDS(ON)	ID=10mA, VGS=4.0V	—	20	50	Ω	
Input Capacitance	Ciss	VDS=5V, VGS=0, f=1MHz	—	6.3	—	pF	
Reverse Transfer Capacitance	Crss	VDS=5V, VGS=0, f=1MHz	—	1.3	—	pF	
Output Capacitance	Coss	VDS=5V, VGS=0, f=1MHz	—	5.7	—	pF	
Switching Time	Turn-on Time	t _{on}	VDD=5V, ID=10mA, VGS=0~4.0V	—	0.11	—	μs
	Turn-off Time	t _{off}	VDD=5V, ID=10mA, VGS=0~4.0V	—	0.15	—	μs

SWITCHING TIME TEST CIRCUIT

